

General Description:

HM4N90I, the silicon N-channel Enhanced VDMOSFETs, is obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-251, which accords with the RoHS standard.

Features:

- Fast Switching
- Low ON Resistance($R_{ds(on)} \leq 3\Omega$)
- Low Gate Charge (Typical Data:25.2nC)
- Low Reverse transfer capacitances(Typical:7.4pF)
- 100% Single Pulse avalanche energy Test

Applications:

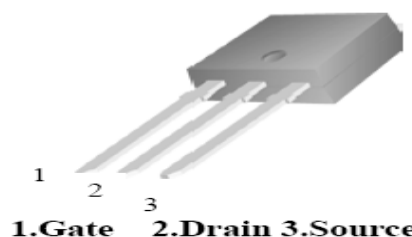
Power switch circuit of adaptor and charger.

Absolute (Tc= 25℃ unless otherwise specified):

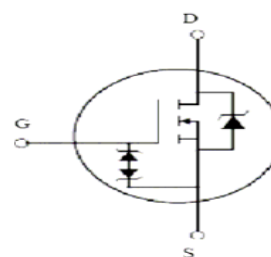
Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	900	V
I_D	Continuous Drain Current	4	A
	Continuous Drain Current T _C = 100 ℃	2.5	A
I_{DM}^{a1}	Pulsed Drain Current	16	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}^{a2}	Single Pulse Avalanche Energy	150	mJ
dv/dt^{a3}	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	100	W
	Derating Factor above 25℃	0.8	W/℃
$V_{ESD(G-S)}$	Gate source ESD (HBM-C= 100pF, R=1.5kΩ)	4000	V
T _J , T _{stg}	Operating Junction and Storage Temperature Range	150, -55 to 150	℃
T _L	Maximum Temperature for Soldering	300	℃

V_{DSS}	900	V
I_D	4	A
$P_D(T_C=25^\circ C)$	100	W
$R_{DS(ON)Typ}$	2.6	Ω

TO-251



Inner Equivalent Principium Chart



Electrical Characteristics (Tc= 25℃ unless otherwise specified):

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Unit
			Min.	Typ.	Max.	
V _{DSS}	Drain to Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	900	--	--	V
Δ BV _{DSS} / Δ T _J	Bvdss Temperature Coefficient	ID=250uA, Reference 25℃	--	0.92	--	V/℃
I _{DSS}	Drain to Source Leakage Current	V _{DS} =900V, V _{GS} = 0V, T _a = 25℃	--	--	25	μA
		V _{DS} =720V, V _{GS} = 0V, T _a = 125℃	--	--	250	μA
I _{GSS(F)}	Gate to Source Forward Leakage	V _{GS} =+20V	--	--	10	μA
I _{GSS(R)}	Gate to Source Reverse Leakage	V _{GS} =-20V	--	--	-10	μA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
R _{DS(ON)}	Drain-to-Source On-Resistance	V _{GS} =10V, I _D =2A	--	2.6	3.0	Ω
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.0	--	4.0	V
Pulse width tp ≤ 300μs, δ ≤ 2%						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g _{fs}	Forward Transconductance	V _{DS} =15V, I _D =2A	--	5	--	S
R _g	Gate resistance	f = 1.0MHz		1.9		Ω
C _{iss}	Input Capacitance	V _{GS} = 0V V _{DS} = 25V f = 1.0MHz	--	835	--	pF
C _{oss}	Output Capacitance		--	76	--	
C _{rss}	Reverse Transfer Capacitance		--	7.4	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
t _{d(ON)}	Turn-on Delay Time	I _D =4A V _{DD} =450V R _G =10Ω	--	16	--	ns
t _r	Rise Time		--	17	--	
t _{d(OFF)}	Turn-Off Delay Time		--	43	--	
t _f	Fall Time		--	14	--	
Q _g	Total Gate Charge	I _D =4A V _{DD} =720V V _{GS} = 10V	--	25.2	--	nC
Q _{gs}	Gate to Source Charge		--	4	--	
Q _{gd}	Gate to Drain ("Miller")Charge		--	12.2	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I _S	Continuous Source Current (Body Diode)		--	--	4	A
I _{SM}	Maximum Pulsed Current (Body Diode)		--	--	16	A
V _{SD}	Diode Forward Voltage	I _S =4A, V _{GS} =0V	--	--	1.5	V
trr	Reverse Recovery Time	I _S =4A, T _j = 25 °C dI _F /dt=100A/us, V _{GS} =0V	--	382	--	ns
Qrr	Reverse Recovery Charge		--	1792	--	nC
I _{RRM}	Reverse Recovery Current		--	9.4	--	A
Pulse width tp≤300μs, δ ≤2%						

Symbol	Parameter	Max.	Units
$R_{\theta JC}$	Junction-to-Case	1.25	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient	100	$^\circ C/W$

^{a1}: Repetitive rating; pulse width limited by maximum junction temperature

^{a2}: $L=10mH, I_D=5.5A, \text{Start } T_j=25^\circ C$

^{a3}: $I_{SD}=4A, di/dt \leq 100A/us, V_{DD} \leq BV_{DS}, \text{Start } T_j=25^\circ C$

Characteristics Curve:

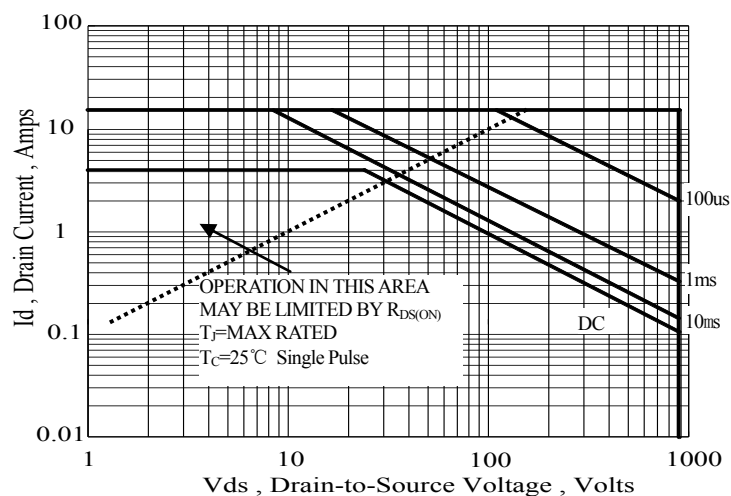


Figure 1 Maximum Forward Bias Safe Operating Area

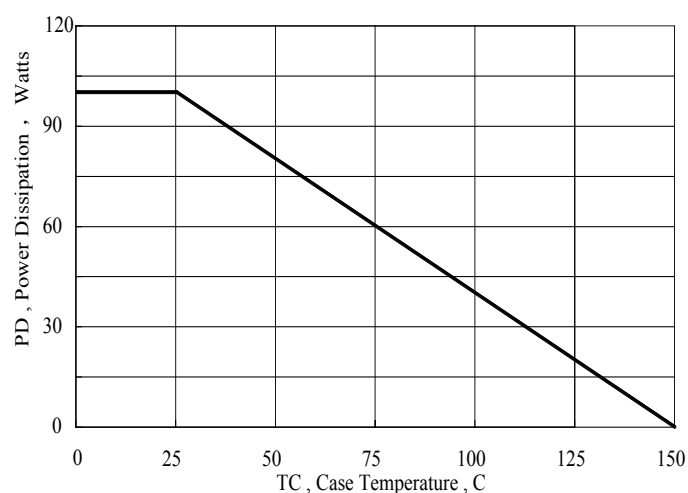


Figure 2 Maximum Power Dissipation vs Case Temperature

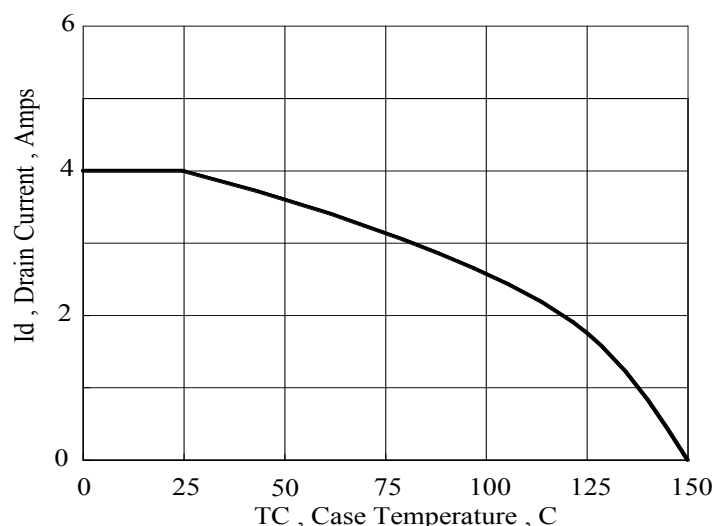


Figure 3 Maximum Continuous Drain Current vs Case Temperature

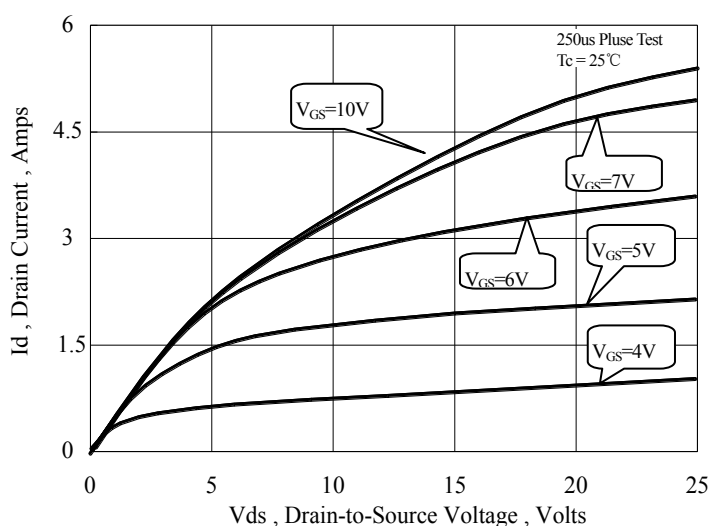
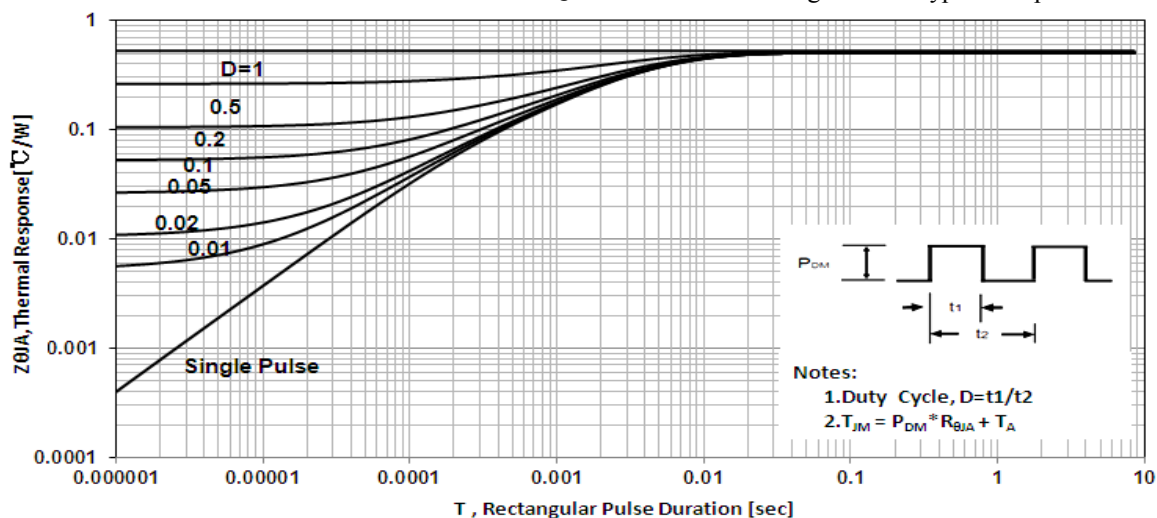


Figure 4 Typical Output Characteristics



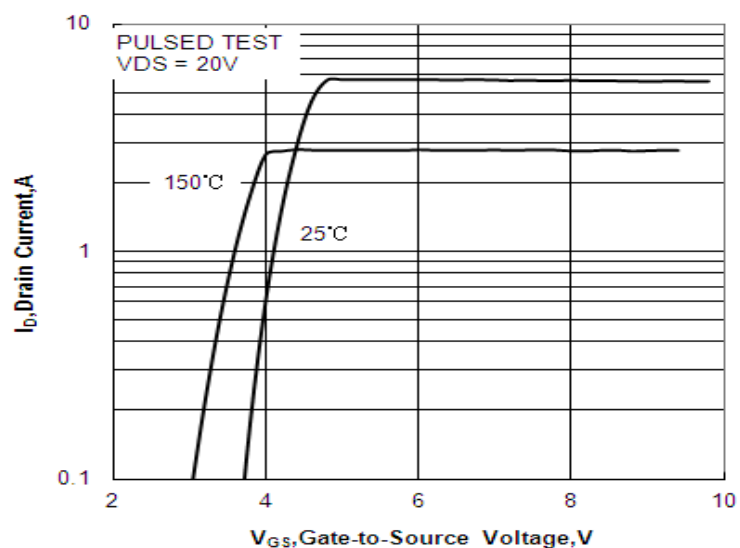


Figure 6 Typical Transfer Characteristics

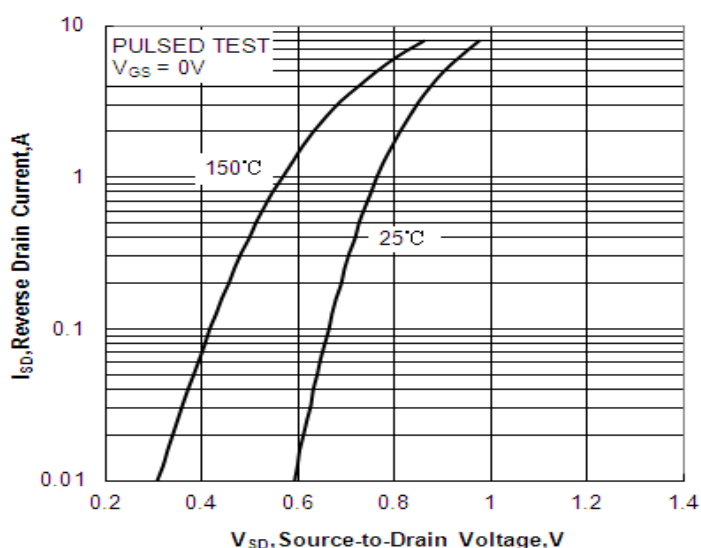


Figure 7 Typical Body Diode Transfer Characteristics

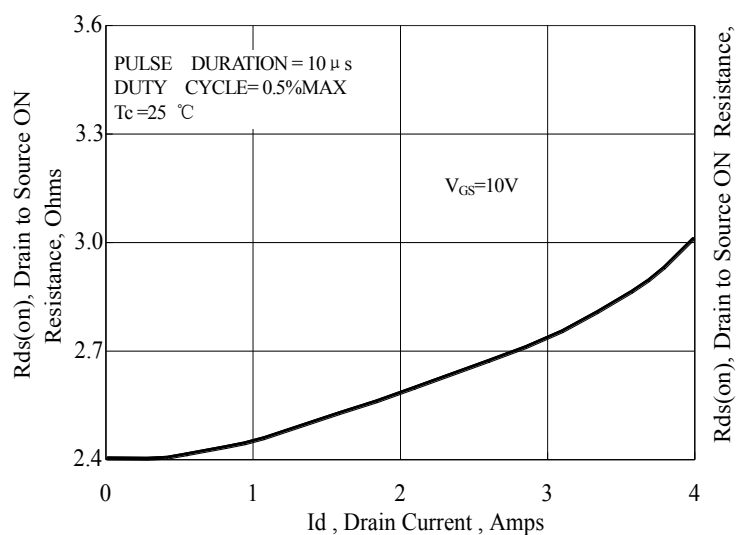


Figure 8 Typical Drain to Source ON Resistance vs Drain Current

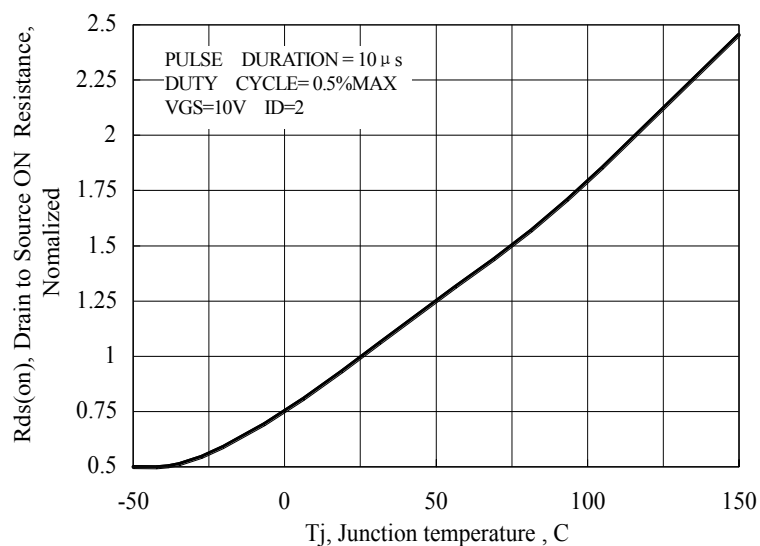


Figure 9 Typical Drain to Source on Resistance vs Junction Temperature

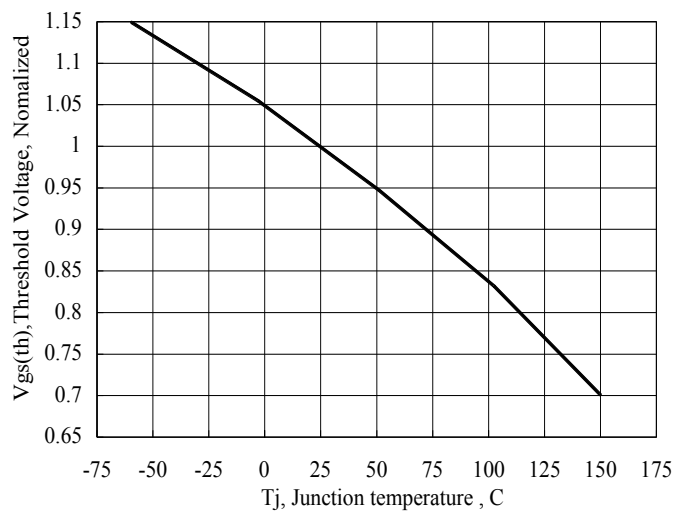


Figure 10 Typical Theshold Voltage vs Junction Temperature

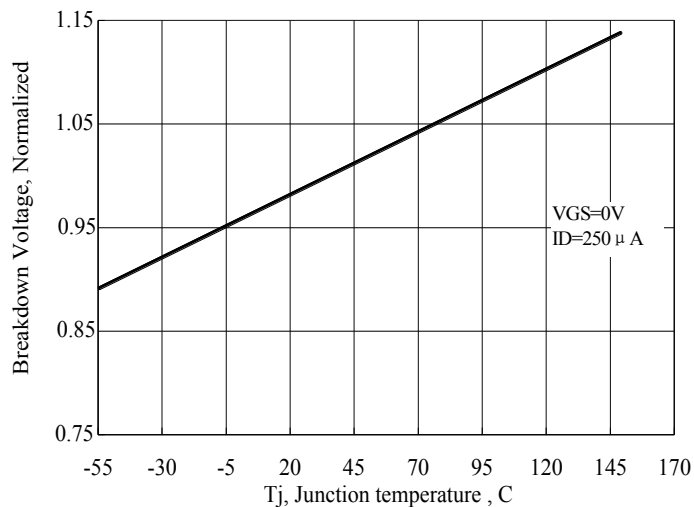


Figure 11 Typical Breakdown Voltage vs Junction Temperature

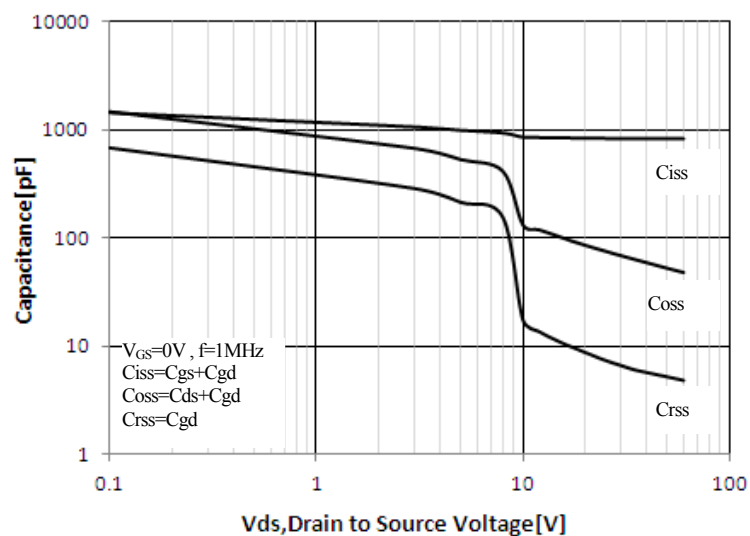


Figure 12 Typical Capacitance vs Drain to Source Voltage

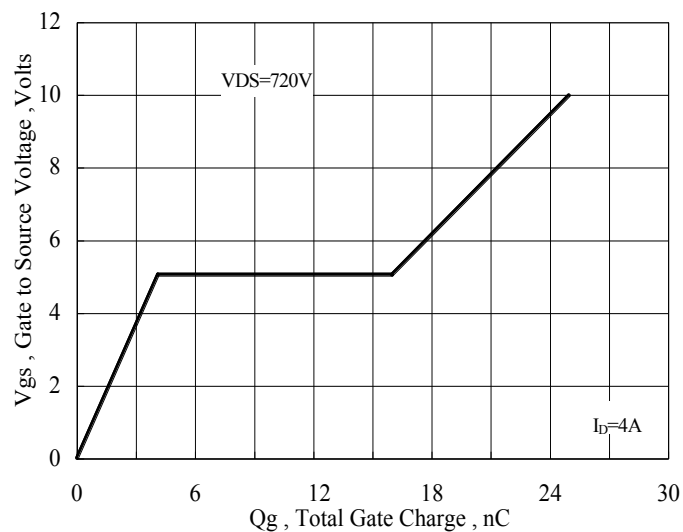


Figure 13 Typical Gate Charge vs Gate to Source Voltage

Test Circuit and Waveform

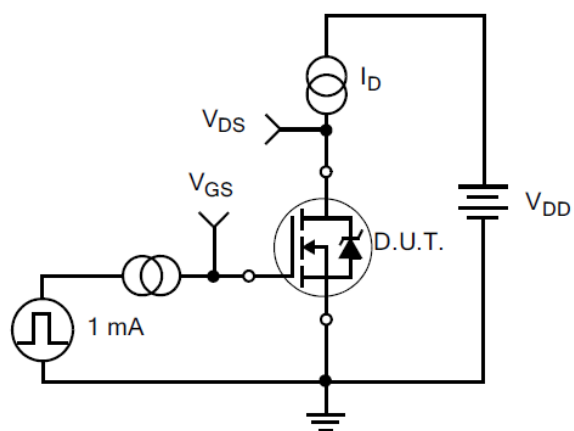


Figure 14. Gate Charge Test Circuit

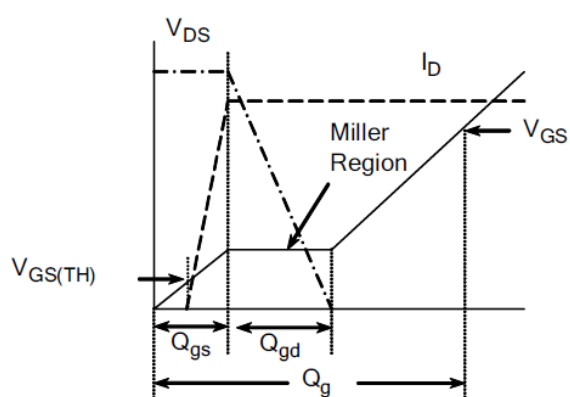


Figure 15. Gate Charge Waveforms

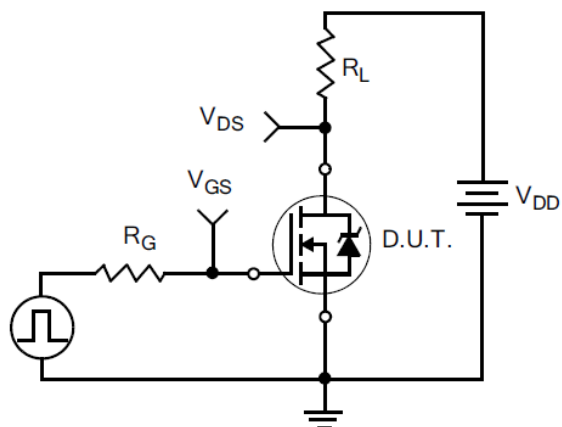


Figure 16. Resistive Switching Test Circuit

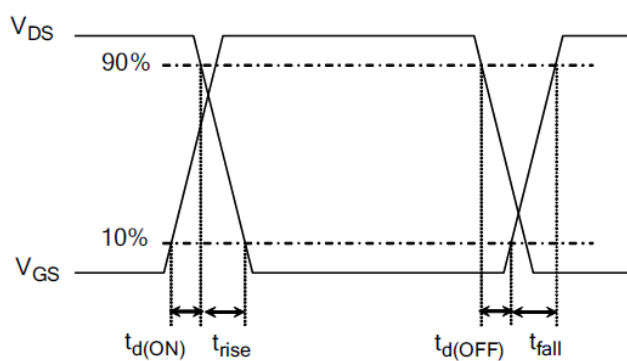


Figure 17. Resistive Switching Waveforms

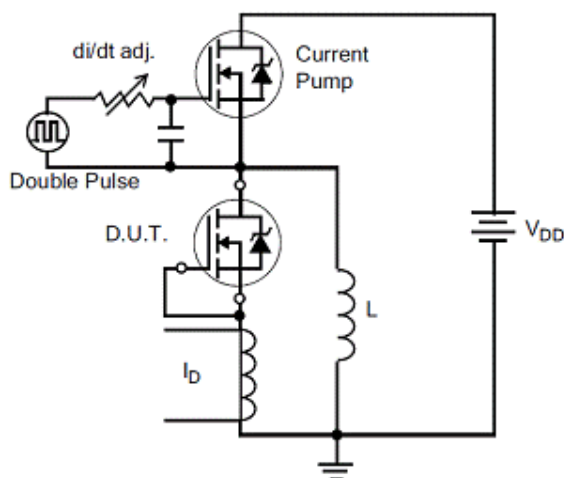


Figure 18. Diode Reverse Recovery Test Circuit

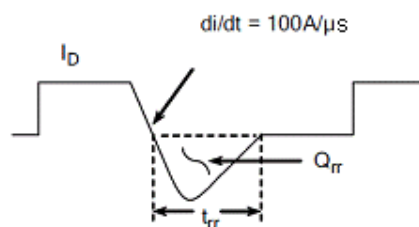


Figure 19. Diode Reverse Recovery Waveform

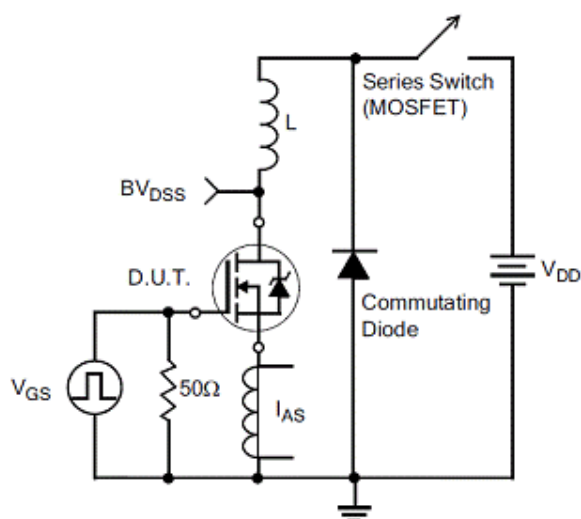


Figure20.Unclamped Inductive Switching Test Circuit

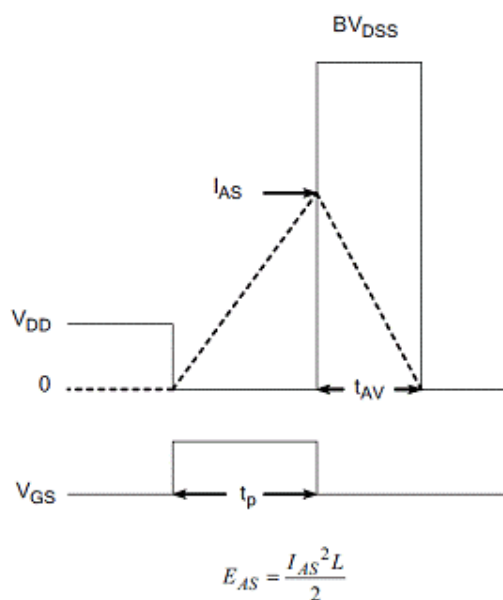
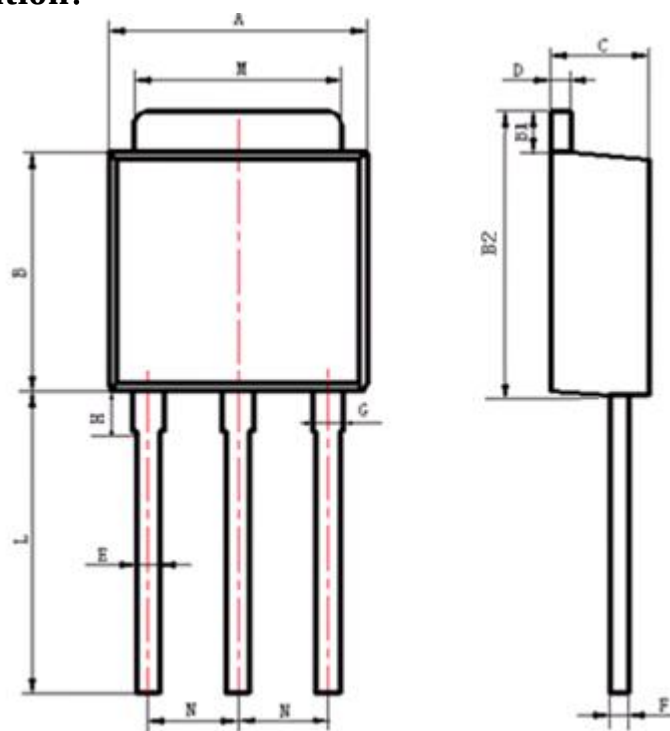


Figure21.Unclamped Inductive Switching Waveform

Package Information:



Items	Values(mm)	
	MIN	MAX
A	6.30	6.90
B	5.20	6.30
B1	0.70	1.30
B2	6.80	7.40
C	2.10	2.50
D	0.30	0.60
E	0.50	0.86
F	0.30	0.60
G	0.70	1.00
H	1.40	2.40
L*	7.50	9.80
M	5.10	5.50
N	2.09	2.49

*: adjustable

TO-251 Package